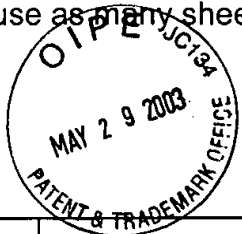


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/073,506	
			Filing Date	February 11, 2002	
			Confirmation Number	6190	
			First Named Inventor	Robert J. Falster	
			Group Art Unit	1775	
			Examiner Name	Matthew A. Anderson	
Sheet	1	of	10	Attorney Docket No.	MEMC 98-1451/2554.1



U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
MA	1	4,314,595		Yamamoto et al.	02/1982
MA	2	4,376,657		Nagasawa et al.	03/1983
MA	3	4,437,922		Bischoff et al.	03/1984
MA	4	4,505,759		O'Mara	03/1985
MA	5	4,548,654		Tobin	10/1985
MA	6	4,851,358		Huber	07/1989
MA	7	4,868,133		Huber	09/1989
MA	8	4,981,549		Yamashita et al.	01/1991
MA	9	5,264,189		Yamashita et al.	11/1993
MA	10	5,327,007		Imura et al.	07/1994
MA	11	5,401,669		Falster et al.	03/1995
MA	12	5,403,406		Falster et al.	04/1995
MA	13	5,445,975		Gardner et al.	08/1995
MA	14	5,474,020		Bell et al.	12/1995
MA	15	5,485,803		Habu	01/1996

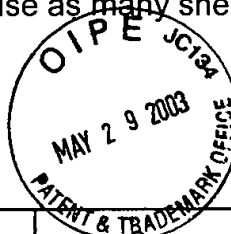
Examiner Signature	Matthew Anderson	Date Considered	8/12/03
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PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) 				Complete if Known	
				Application Number	10/073,506
				Filing Date	February 11, 2002
				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	Matthew A. Anderson
Sheet	2	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

MA	16	5,487,354		von Ammon et al.	01/1996
MA	17	5,502,010		Nadahara et al.	03/1996
MA	18	5,502,331		Inoue et al.	03/1996
MA	19	5,534,294		Kubota et al.	07/1996
MA	20	5,539,245		Imura et al.	07/1996
MA	21	5,593,494		Falster	01/1997
MA	22	5,611,855		Wijaranakula	03/1997
MA	23	5,667,584		Takano et al.	09/1997
MA	24	5,674,756		Satoh et al.	10/1997
MA	25	5,704,973		Sakurada et al.	01/1998
MA	26	5,728,211		Takano et al.	03/1998
MA	27	5,738,942		Kubota et al.	04/1998
MA	28	5,788,763		Hayashi et al.	08/1998
MA	29	5,919,302		Falster et al.	07/06/1999
MA	30	5,935,320		Graef et al.	08/10/1999
MA	31	5,939,770		Kageyama	08/1999
MA	32	5,942,032		Kim et al.	08/24/1999
MA	33	5,944,889		Park et al.	08/1999
MA	34	5,954,873		Hourai et al.	09/1999
MA	35	5,968,262		Saishouji et al.	10/1999

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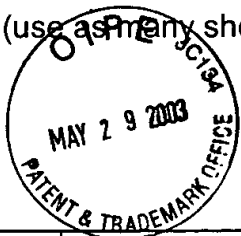
Examiner Signature	<i>Matthew Anderson</i>	Date Considered	8/12/07
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PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/073,506
				Filing Date	February 11, 2002
				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	Matthew A. Anderson
Sheet	3	of	10	Attorney Docket No.	MEMC 98-1451/2554.1



MA	36	5,968,264		Lida et al.	10/1999
MA	37	6,045,610		Park et al.	04/2000
MA	38	6,053,974		Luter et al.	04/25/2000
MA	39	6,093,913		Schrenker et al.	07/25/2000
MA	40	6,153,008		von Ammon et al.	11/28/2000
MA	41	6,190,631	B1	Falster	02/20/2001
MA	42	6,228,164		von Ammon et al.	05/08/2001
MA	43	6,254,672	B1	Falster et al.	07/03/2001
MA	44	6,287,380	B1	Falster et al.	09/11/2001

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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
MA	45	EP	0 504 837	A2		09/1992	
MA	46	EP	0 503 816	B1		09/1992	
MA	47	EP	0 536 958	A1		04/1993	
MA	48	EP	0 716 168	A1		06/1996	
MA	49	EP	0 747 513	A2	Shin-Estu Handotai Company Ltd.	12/11/1996	
MA	50	EP	0 799 913	A1		10/1997	

Examiner Signature	<i>Matthew A. Anderson</i>	Date Considered	8/12/03
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**INFORMATION DISCLOSURE
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Application Number	10/073,506
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Confirmation Number	6190
First Named Inventor	Robert J. Falster
Group Art Unit	1775
Examiner Name	Matthew A. Anderson
Attorney Docket No.	MEMC 98-1451/253

Sheet 4 of 10

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NA	51	EP	0 890 662		Shinetsu Handotai KK	01/13/1999	
NA	52	EP	0 909 840		Shinetsu Handotai KK	04/21/1999	
NA	53	EP	0 962 557	A1	Shin-Etsu Handotai Company Ltd.	05/21/1999	
NA	54	EP	0 962 556	A1		08/1999	
NA	55	DE	39 05 626	A1		08/1989	
NA	56	DE	43 23 964	A1		01/1994	
NA	57	DE	44 14 947	A1		08/1995	
NA	58	DE	198 06 045	A1		08/1998	
NA	59	JP	2-180789			07/1990	
NA	60	JP	Hei 3-93700		Nippon Steel Corp.	04/18/1991	
NA	61	JP	4-108682			04/1992	
NA	62	JP	Hei 7-041383		Nippon Steel Corp.et al.	02/10/1995	
NA	63	JP	Hei 7-206591		Nippon Steel Corp.et al.	08/08/1995	
NA	64	JP	7321120 (Abstract Only)			12/1995	
NA	65	JP	7335657 (Abstract Only)			12/1995	
NA	66	JP	8045947 (Abstract Only)			02/1996	
NA	67	JP	8045944 (Abstract Only)			02/1996	
NA	68	JP	8-045945			02/1996	

Examiner Signature	Matthew Anderson	Date Considered	8/12/03
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Complete if Known

Application Number	10/073,506
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Confirmation Number	6190
First Named Inventor	Robert J. Falster
Group Art Unit	1775
Examiner Name	Matthew A. Anderson
Attorney Docket No.	MEMC 98-1451/2554.1

Sheet 5 of 10

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69	JP	Hei 8-208374		Nippon Steel Corp. et al	08/13/1996
70	JP	HO 8-268794		Sumitomo Sitix Corp.	10/15/1996
71	JP	8-330316 (Pub. Hei 07-158458)		Sumitomo Sitix Corp.	12/1996
72	JP	9-199416			07/1997
73	JP	9-202690			08/1997
74	JP	11-150119	A		06/1999
75	JP	11-157995	A		06/1999
76	JP	11-180800	A		07/1999
77	JP	11-189495	A		07/1999
78	JP	11-199386	A		07/1999
79	JP	11-199387	A		07/1999
80	WO	97/26393			07/1997
81	WO	98/45507			10/1998
82	WO	98/45508			10/1998
83	WO	98/45509			10/1998
84	WO	98/45510			10/1998
85	GB	2 137 524	A	Hitachi Ltd. (Japan)	10/10/1984
86	GB	2182 262 A			05/1987

OTHER ART - NON PATENT LITERATURE DOCUMENTS

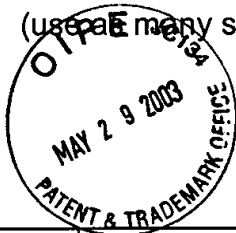
Examiner Signature	<i>Matthew Anderson</i>	Date Considered	8/12/03
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PTO/SB/08A				Compleat if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/073,506
				Filing Date	February 11, 2002
				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	Matthew A. Anderson
Sheet	6	of	10	Attorney Docket No.	MEMC 98-1451/2554.1



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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
MAA	87	ABE, et al., "Defect-Free Surfaces of Bulk Wafers by Combination of RTA and Crystal Growth", (publication information unknown).	
MAA	88	ABE, et al., "Innovated Silicon Crystal Growth and Wafering Technologies", Electrochemical Society Proceedings, Volume 97, No. 3, pp. 123-133.	
MAA	89	ABE, T., et al., "Behavior of Point Defects in FZ Silicon Crystals", Semiconductor Silicon 1990, <i>Proceedings of the Sixth International Symposium on Silicon Materials Science and Technology</i> , Vol. 90-7 (1990), pp. 105-116	
MAA	90	DE KOCK, A.J.R., "The Elimination of Vacancy-Cluster Formation in Dislocation-Free Silicon Crystals", J. of the Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, Vol. 118, No. 11, (Nov. 1971), pp.1851-1856	
MAA	91	DE KOCK, A.J.R., et al., "Effect of Growth Parameters on Formation and Elimination of Vacancy Clusters in Dislocation-Free Silicon Crystals", Journal of Crystal Growth, Vol. 22 (1974), pp. 311-320	
MAA	92	DE KOCK, A.J.R., "Point Defect Condensation in Dislocation-Free Silicon Crystals", Semiconductor Silicon, 1977, pp. 508-520.	
MAA	93	DE KOCK, et al., "The Effect of Doping on the Formation of Swirl Defects in Dislocation-Free Czochralski-Grown Silicon crystals", Journal of Crystal Growth, Vol. 49, pp. 718-734 (1980).	
MAA	94	DORNBERGER et al., "The Dependence of Ring Like Distributed Stacking Faults on the Axial Temperature Gradient of Growing Czochralski Silicon Crystals", Electrochemical Society Proceedings, Volume 95-4, pp. 294-305 (1995).	
MAA	95	DORNBERGER, E., et al., "Simulation of Grown-In Voids in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Volume 97, No. 22, pp. 40-49	
MAA	96	DORNBERGER, E., et al., "The Impact of Dwell Time Above 900°C During Crystal Growth on the Gate Oxide Integrity of Silicon Wafers", Electrochemical Society Proceedings, Volume 96, No. 13, pp. 140-151.	

Examiner Signature	<i>Matthew A. Anderson</i>	Date Considered	8/12/03
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			Confirmation Number	6190	
			First Named Inventor	Robert J. Falster	
			Group Art Unit	1775	
			Examiner Name	Matthew A. Anderson	
Sheet	7	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

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TC 1700

MA	97	DORNBERGER, E., et al., "Simulation of Non-Uniform Grown-In Void Distributions in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Vol. 98, Vol. 1, pp. 490-503	
MA	98	EIDENZON, A.M., et al., "Influence of growth rate on swirl defects in large dislocation-free crystals of silicon grown by the Czochralski method" Soviet Physics Crystallography, Vol. 30(5), (1985), pp. 576-580	
MA	99	EIDENZON, A.M., et al., "Defect-Free Silicon Crystals Grown by the Czochralski Technique" Inorganic Materials, Vol. 33-3 (1997) pp. 219-225	
MA	100	FOLL, H., et al. "The Formation of Swirl Defects in Silicon by Agglomeration of Self-Interstitials", Journal of Crystal Growth, 1977, pp. 90-1087, Vol. 40, North-Holland Publishing Company	
MA	101	Hara, et al., "Enhancement of Oxygen Precipitation in Quenched Czochralski Silicon Crystals", J. Appl. Phys., Vol. 66, No. 8, pp. 3958-3960 (1989).	
MA	102	HOURAI, M., et al., "Improvement of Gate Oxide Integrity Characteristics of CZ-Grown Silicon Crystals", Progress in Semiconductor Fabrication presented by: Semiconductor Equipment and Materials International, Semicon/Europa 93, March 30-April 1, 1993, Geneva, Switzerland	
MA	103	HOURAI, M., et al. "Growth Parameters Determining the Type of Grown-In Defects in Czochralski Silicon Crystals", Materials Science Forum, Vols. 196-201 (1995) pp. 1713-1718	
MA	104	International Search Report for Application No. PCT/US 99/24068 dated October 13, 1999, 7 pages.	
MA	105	IZUNOME K., et al., "Light Point Defects on Hydrogen Annealed Silicon Wafer, Jpn. J. Appl. Phys. Vol. 36, pp. L1127-L1129, 1997	
MA	106	JACOB, et al., "Determination of Vacancy Concentrations in the Bulk of Silicon Wafers by Platinum Diffusion Experiments", J. Appl. Phys., Vol. 82, No. 1, pp. 182-191 (1997).	
MA	107	KISSINGER, et al., "A Method for Studying the Grown-In Defect Density Spectra in Czochralski Silicon Wafers", J. Electrochem. Soc., Vol. 144, No. 4, pp. 1447-1456 (1997).	
MA	108	LEMKE, H., et al., "Analytical Approximations for the Distributions of Intrinsic Point Defects in Grown Silicon Crystals", Phys. Stat. Sol. (a) Vol. 176 (1999), pp. 843-865	

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PTO/SB/08A			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/416,998	
			Filing Date	October 13, 1999	
			Confirmation Number	6867	
			First Named Inventor	Robert J. Falster et al.	
			Group Art Unit	1765	
			Examiner Name		
Sheet	8	of	10	Attorney Docket No.	MEMC 98-145 (2554.1)

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	109	MIYAZAKI M., et al., "Microstructure Observation of 'Crystal-Originated Particles' on Silicon Wafers", Jpn. J. Appl. Phys., Vol. 34, pp. 6303-6307, 1995	
	110	NAKAMURA, Kozo, et al., "Formation Process of Grown-In Defects in Czochralski Grown Silicon Crystals", Journal of Crystal Growth, Vol. 180, pp. 61-72, 1997.	
	111	PARK, J.G., et al., "Nature of D-Defect in CZ Silicon: D-Defect Dissolution and D-Defect Related T.D.D.B.", Material Science Forum, Vol.s. 196-201, 1995, pp. 1697-1706.	
	112	PARK, J.G., et al., "Effect of Crystal Defects on Device Characteristics", <i>Proceedings of the Symposium on Crystalline Defects and Contamination: Their Impact And Control In Device Manufacturing II</i> , Proceed. Vol. 97-22 (1997), pp.173-195	
	113	PUZANOV, N.I., et al., "Influence of Transitional Crystallization Regimes on Microdefects in Silicon", USSR Academy of Sciences Newsletter, Vol. 22, No. 8 (1986), pp.1237-1242	X
	114	PUZANOV, N.I., et al., "Relaxation In A System Of Point Defects In A Growing Dislocation-Free Crystal Of Silicon", Sov. Phys. Crystallogr., Vol. 31, No. 2, (1986) pp. 219-222.	
	115	PUZANOV, N.I., et al., "The effect of thermal history during crystal growth on oxygen precipitation in Czochralski-grown silicon", Semicond. Sci. Technol., Vol. 7, (1992), pp. 406-413	
	116	PUZANOV, N., et al., "Formation of the bands of anomalous oxygen precipitation in Czochralski-grown Si crystals" Journal of Crystal Growth vol. 137, (1994), pp. 642-652	
	117	PUZANOV, N., et al., "The Role of Intrinsic Point Defects in the Formation of Oxygen Precipitation Centers in Dislocation-Free Silicon" Crystallography Reports, Vol. 41, No. 1, (1996), pp. 134-141	
	118	PUZANOV, N.I., et al., "Cultivation, Morphology and Structural Integrity of Dislocation-Free Silicon Tetracrystals", Inorganic Materials, Vol. 32, No. 8 (1996), pp. 903-912	X
	119	PUZANOV, N.L., et al., "Harmful Microdefects in the Seed-End Portion of Large-Diameter Silicon Ingots", Inorganic Materials, Vol. 33, No. 8, (1997) pp. 765-769	
	120	PUZANOV, N., et al., "Modelling microdefect distribution in dislocation-free Si crystals grown from the melt", Journal of Crystal Growth, 178, (1997), pp. 468-478	

Examiner Signature		Date Considered	8/12/03
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PTO/SB/08A			Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/416,998
			Filing Date	October 13, 1999
			Confirmation Number	6867
			First Named Inventor	Robert J. Falster et al.
			Group Art Unit	1765
			Examiner Name	
Sheet 9	of 10	Attorney Docket No. MEMC 96-1451 (2554.1) RECEIVED JUN 09 2003 TC 1700		

121	121	PUZANOV, N., et al., "Role of Vacancies in the Nucleation of Ringlike-patterned Oxidation-induced Stacking Faults in Melt-grown Silicon Crystals" Inorganic Materials, Vol. 34-4, (1998) pp. 307-314	
122	122	ROKSNOER, P.J., "Microdefects in a Non-Striated Distribution in Floating-Zone Silicon Crystals", Journal of Crystal Growth, Vol. 53 (1981), pp. 563-573	
123	123	ROKSNOER, P.J., "The Mechanism of Formation of Microdefects in Silicon", Journal of Crystal Growth, Vol. 68 (1984), pp. 596-612	
124	124	SHIMANUKI, Y., et al., "Effects of Thermal History on Microdefect Formation in Czochralski Silicon Crystals", Japanese Journal of Applied Physics, Vol. 24, No. 12, (1985), pp. 1594-1599	
125	125	SINNO, T., et al., "On the Dynamics of the Oxidation-Induced Stacking-Fault Ring in as-grown Czochralski silicon crystals", Applied Physics Letters, Vol. 70, No. 17, pp. 2250-2252, 1997.	
126	126	SINNO, T., et al., "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals", J. Electrochem. Soc., Vol. 145, No. 1, pp. 302-318, 1998.	
127	127	TAKANO, K., et al., "Relationship Between Grown-in Defects and Thermal History During CZ Si Crystal Growth", Materials Science Forum, Vols. 196-201, 1995, pp. 1707-1712.	
128	128	TAN, T. Y., "Point Defects, Diffusion Processes, and Swirl Defect Formation in Silicon", Appl. Phys. A., Vol. 37, pp. 1-17, 1985.	
129	129	VANHELLEMONT, J., et al., "Defects in As-Grown Silicon and Their Evolution During Heat Treatments", Materials Science Forum, Vols. 258-263, pp. 341-346, 1997.	
130	130	von AMMON et al., "The Dependence of Bulk Defects on the Axial Temperature Gradient of Silicon Crystals During Czochralski Growth", Journal of Crystal Growth, Vol. 151, pp. 273-277 (1995).	
131	131	von AMMON et al. "Bulk properties of very large diameter silicon single crystals" Journal of Crystal Growth, Vol. 198/199, (1999), pp. 390-398	
132	132	VORONKOV, V., et al., "Behaviour and Effects of Intrinsic Point Defects in the Growth of Large Silicon Crystals", Electrochemical Society Proceedings, Volume 97-22, pp. 3-17 (1997).	
133	133	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643 (1982).	

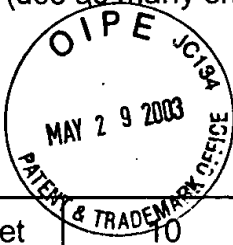
Examiner Signature	<i>Matthew Anderson</i>	Date Considered	8/12/03
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Sheet	10	of	10	Attorney Docket No.	MEMC 98-1451 (2554.1)



	134	WIJARANAKULA, W., "Effect of high-temperature annealing on the dissolution of the D-defects in n-type Czochralski silicon", Appl. Phys. Lett., Vol. 68, No. 8, (1994), pp.1030-1032	
	135	WIJARANAKULA, W., "Numerical Modeling of the Point Defect Aggregation during the Czochralski Silicon Crystal Growth", Journal of Electrochemical Society, Vol. 139, No. 2 (Feb. 1992), pp.604-616	
	136	WINKLER, et al., "Improvement of the Gate Oxide Integrity by Modifying Crystal Pulling and Its Impact on Device Failures", J. Electrochem. Soc., Vol. 141, No. 5, pp. 1398-1401 (1994).	
	137	YAMAGISHI, et al., "Recognition of D Defects in Silicon Single Crystals by Preferential Etching and Effect on Gate Oxide Integrity", Semicond. Sci Technol. 7, 1992, A135-A140.	
	138	YAMAUCHI, et al., "Application of Copper-Decoration Method to Characterize As-Grown Czochralski-Silicon", Jpn. J. Appl. Phys., Vol. 31, 1992, pp. L439-L442.	
	139	ZIMMERMAN, H., et al. "Gold and Platinum Diffusion: the Key to the Understanding of Intrinsic Point Defect Behavior in Silicon", Applied Physics A Solids and Surfaces, Vol. A55, No. 1 (1992) pp. 121-134	
	140	ZIMMERMAN, H., et al. "Vacancy concentration wafer mapping in silicon" Journal of Crystal Growth, Vol. 129, (1993) pp. 582-592.	

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